

Package: QFN, 16 pin, 0.8mmx3mmx3mm

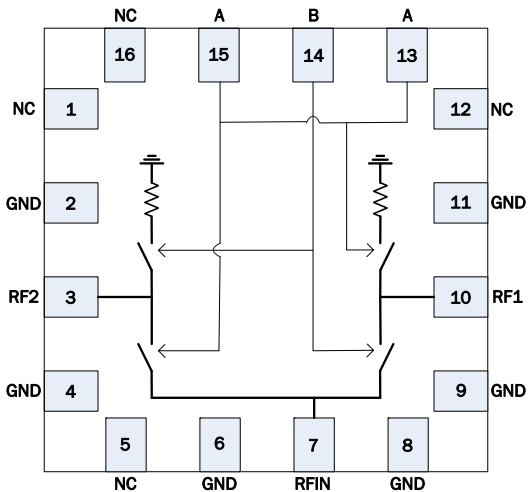


Features

- Low Insertion Loss: 2.25 dB at 20GHz
- High Isolation: 26dB at 20GHz
- Excellent Return Loss
- 21nS Switching Speed
- GaAs pHEMT Technology
- Compact 3mmx3mm QFN package

Applications

- Broadband Communications
- Test Instrumentation
- Fiber Optics
- Military
- Aerospace



Functional Block Diagram

Product Description

RFMD's RFSW2043 is a broadband absorptive SPDT GaAs microwave monolithic integrated circuit (MMIC) switch designed to operate from DC to 20GHz using the RFMD FD05 0.5µm switch process. It features low insertion loss of 2.25dB at 20GHz and high isolation of 26dB at 20GHz while being packaged in a compact low cost 3mmx3mm QFN package for easy end use assembly. The switch uses complementary control logic of -5/0V and does not require a separate bias supply.

Ordering Information

RFSW2043S2	2-piece sample bag
RFSW2043SB	5-piece bag
RFSW2043SQ	25-piece bag
RFSW2043SR	100 pieces on 7" reel
RFSW2043TR7	750 pieces on 7" reel
RFSW2043PCK-410	Evaluation board with a 2-piece sample bag

Optimum Technology Matching® Applied

- | | | | |
|--------------------------------------|--------------------------------------|--|------------------------------------|
| <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input checked="" type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | <input type="checkbox"/> BIFET HBT |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | <input type="checkbox"/> LDMOS |

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Absolute Maximum Ratings

Parameter	Rating	Unit
Drain Bias Voltage (V_{CTRL})	-10	V_{DC}
RF Input Power (Any State)	+30	dBm
RF Output Power (ON State)	+30	dBm
RF Output Power (OFF State)	+21	dBm
Storage Temperature	-55 to +150	°C
Operating Temperature	-55 to +85	°C
ESD JESD22-A114 Human Body Model (HBM)	Class 1A (All pads)	



Caution! ESD sensitive device.

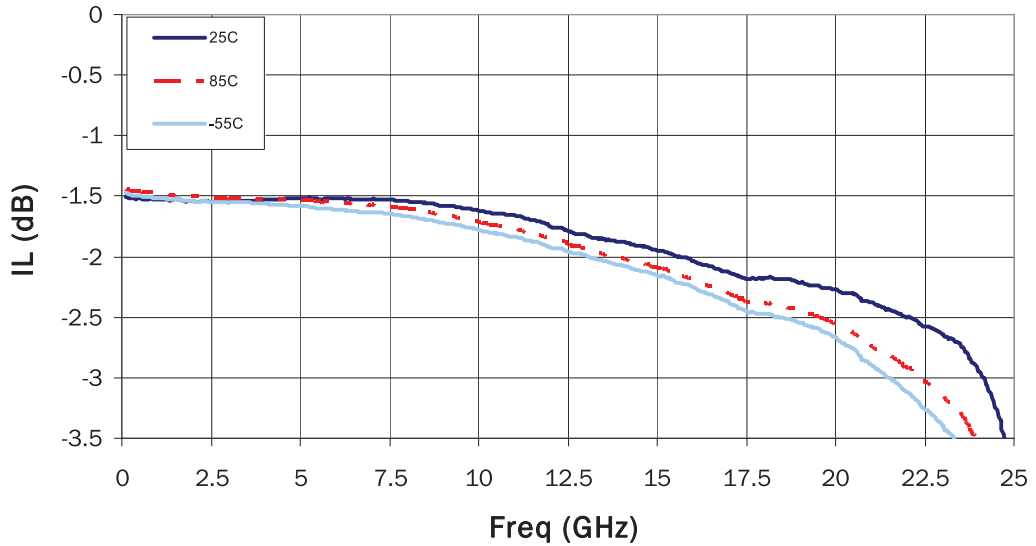
Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

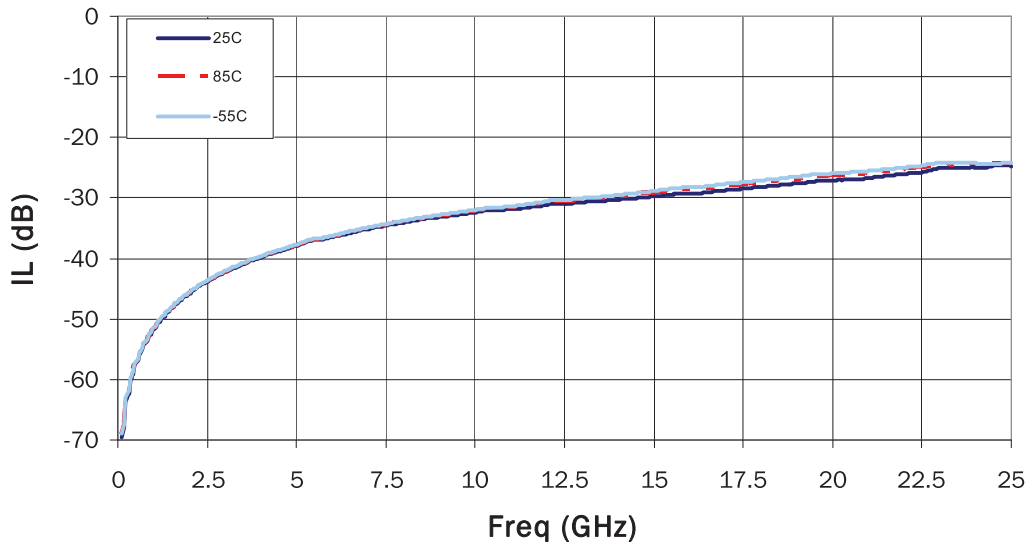
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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Operating Frequency	DC		20	GHz	
Insertion Loss (0GHz to 5GHz)		1.5	1.7	dB	ON State, All Temps
Insertion Loss (5GHz to 10GHz)		1.6	1.9	dB	ON State, All Temps
Insertion Loss (10GHz to 15GHz)		1.8	2.3	dB	ON State, All Temps
Insertion Loss (15GHz to 20GHz)		2.25	2.8	dB	ON State, All Temps
Isolation (DC to 20GHz)	20	30		dB	ON State, All Temps
Input Return Loss (DC to 20GHz)	10	16		dB	ON State, All Temps
Output Return Loss (DC to 20GHz)	12	16		dB	ON State, All Temps
Output Return Loss (DC to 20GHz)	15	22		dB	OFF State, All Temps
OIP3 (2GHz to 20GHz)	40	46		dBm	100MHz spacing, 2dBm input, 25 °C
OIP2 (3GHz to 20GHz)	75	82		dBm	100MHz spacing, 2dBm input, 25 °C
Switching Speed		21	25	ns	50% control to 90% RF, All Temps
Control Current		41	55	µA	Sum of all control lines, 25 °C
Control Voltage		0/-5		V	

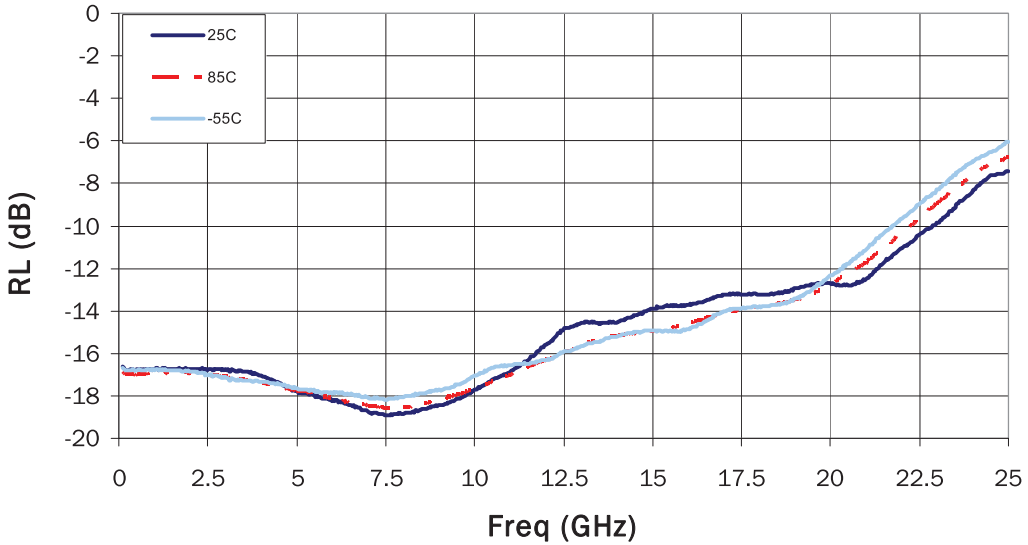
Insertion Loss vs Temp (Vcontrol = -5v)



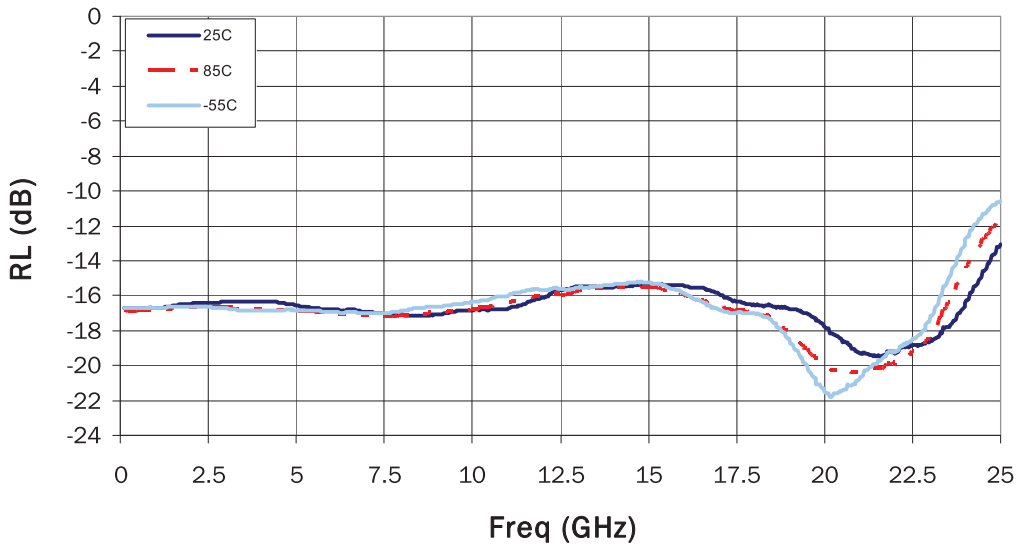
Isolation vs Temp (Vcontrol = -5v)



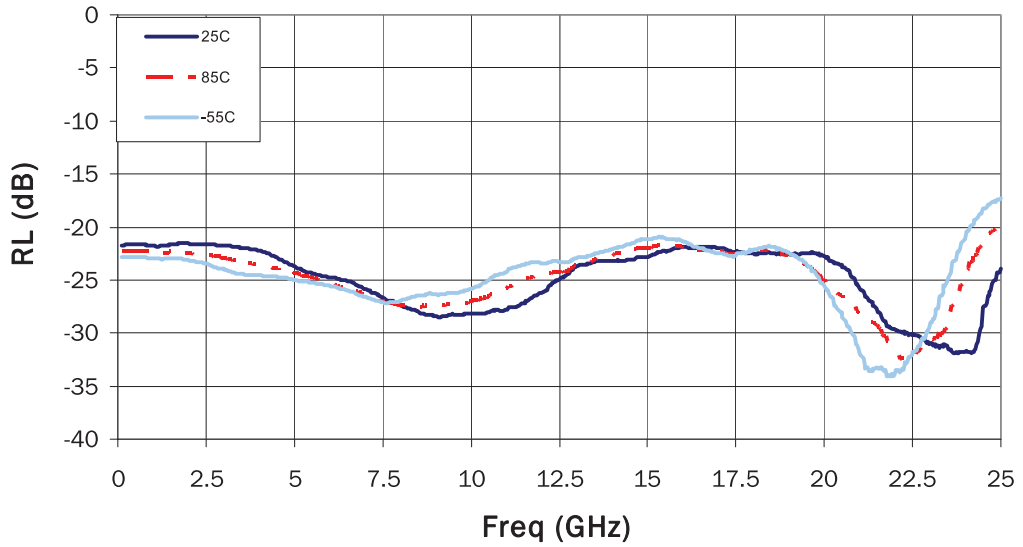
Input Return Loss vs Temp (Vcontrol = -5v)



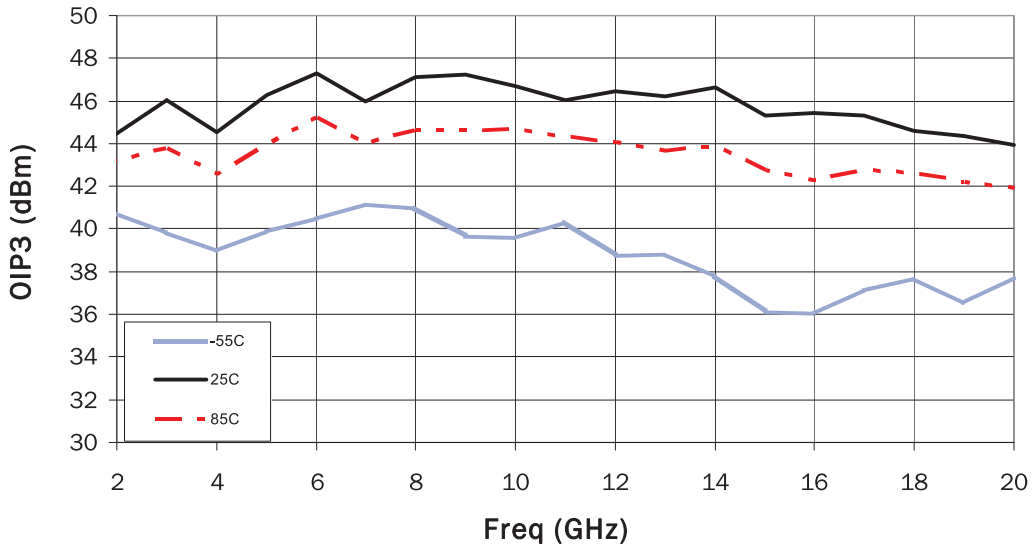
Output Return Loss vs Temp (Vcontrol = -5v)



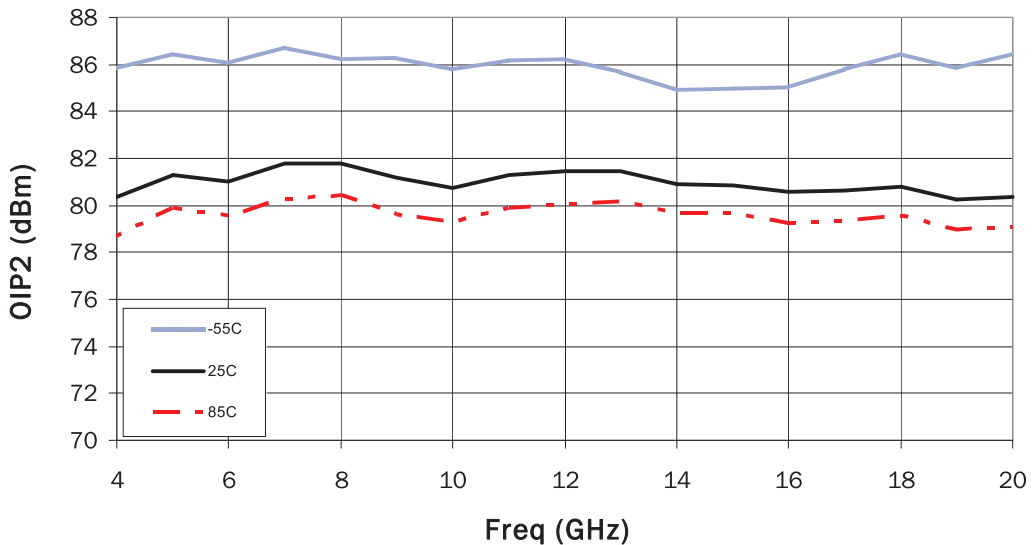
Output Return Loss vs Temp (OFF State, Vcontrol = -5v)

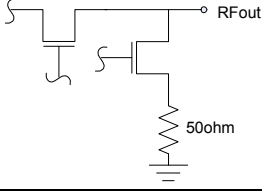
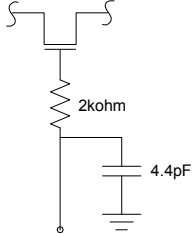
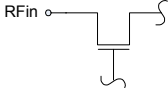


OIP3 vs Temp (Vcontrol = -5V)



OIP2 vs Temp (Vcontrol = -5V)



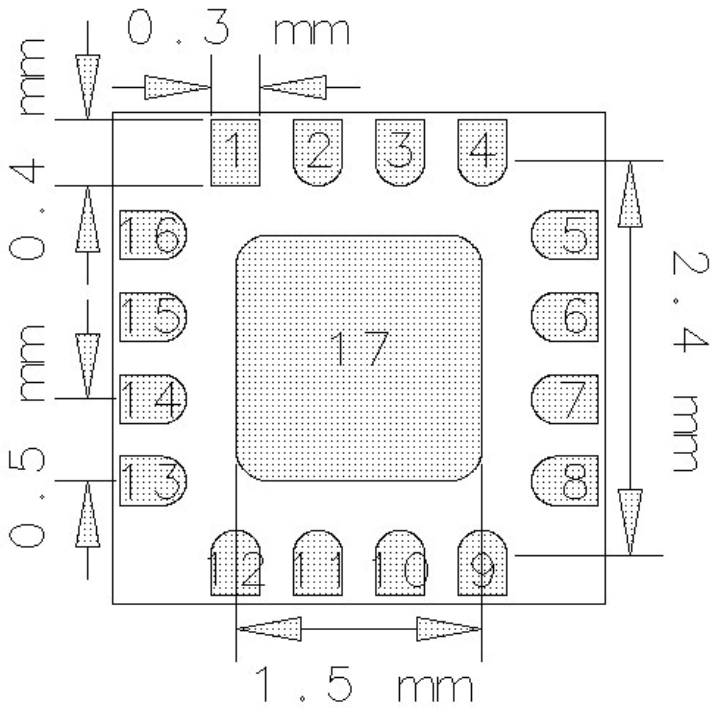
Pin	Function	Description	Interface Schematic
1, 5, 12, 16	NC	No Connect	
2, 4, 6, 8, 9, 11	GND	Ground. Grounding via should be located as close as possible to this pin.	
3, 10	RF2, RF1	RF output. These pins are DC coupled and matched to 50Ω from DC to 20GHz.	
13, 14, 15	VA, VB, VA	DC control for switch operation. Nominal operating voltage is -5V. The two VA pins (13 and 15) are connected internally for added layout flexibility.	
7	RFIN	RF input. This pin is DC coupled and matched to 50Ω from DC to 20GHz.	

Truth Table

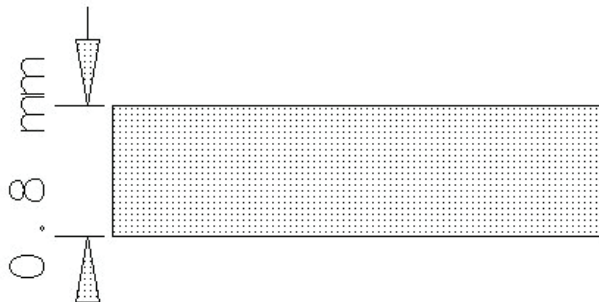
High = -5V ±0.2V, Low = 0V, ±0.2V

Control Line		RF Path
VA	VB	
High	Low	RFin to RF1
Low	High	RFin to RF2

Package Drawing



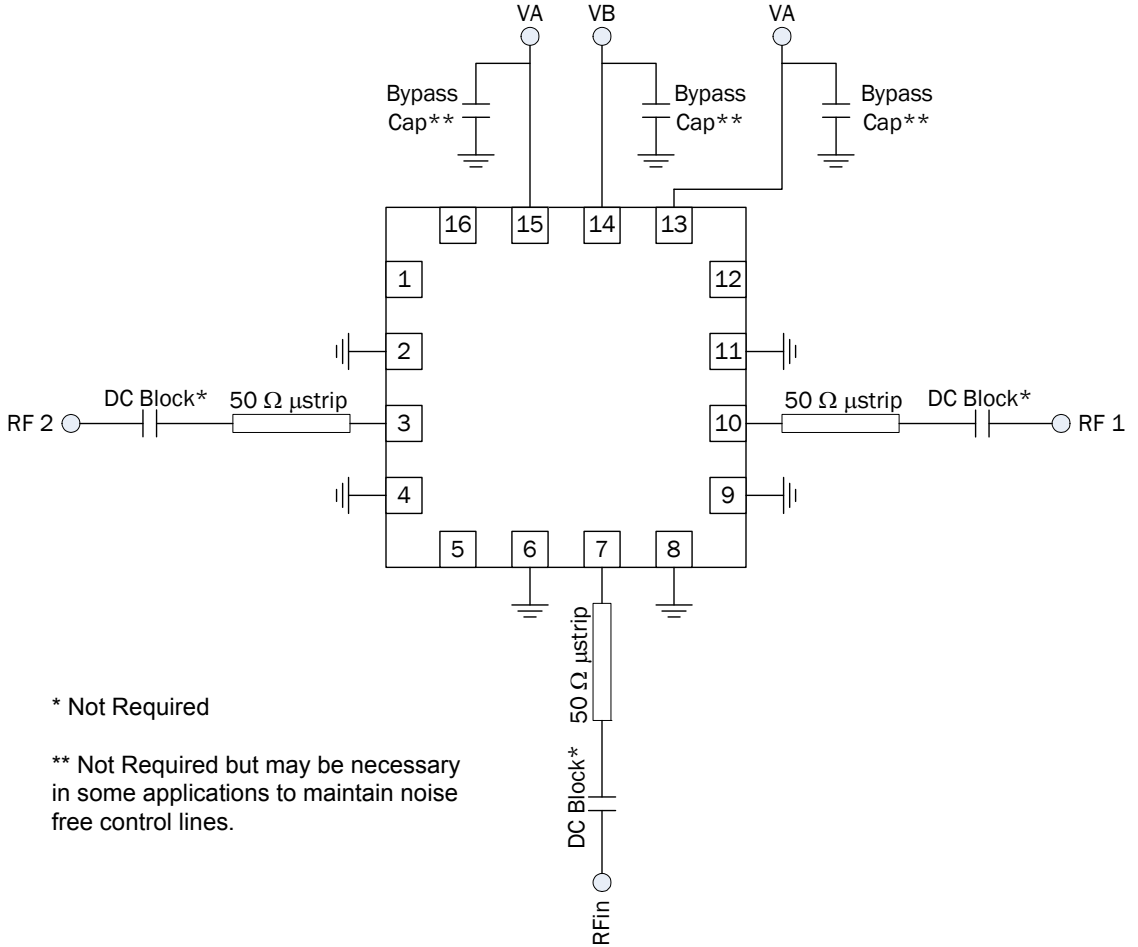
Bottom View



Side View

Maximum Height=1.0mm
Dimensional Tolerance=+0.05mm

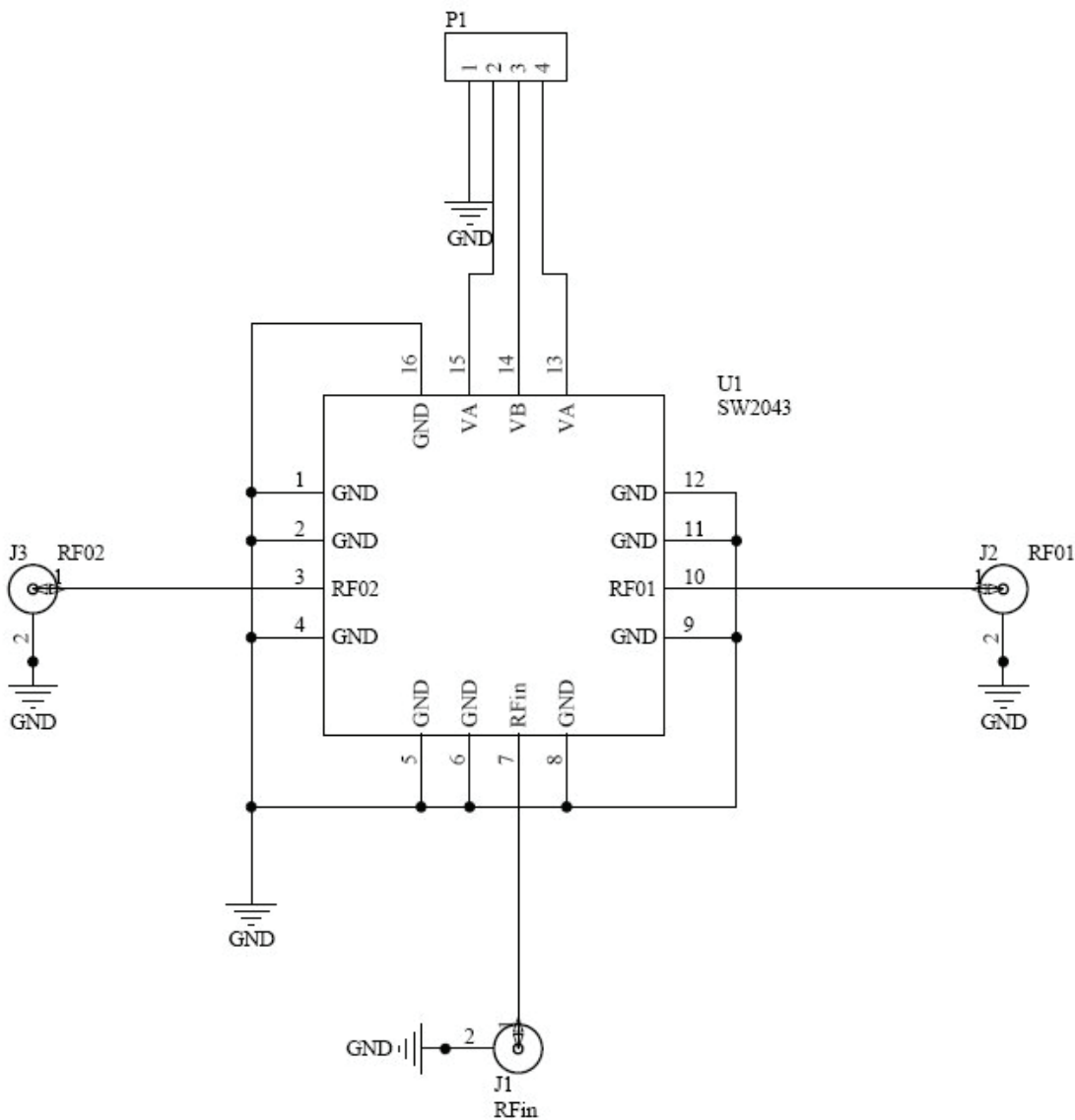
Application Schematic



* Not Required

** Not Required but may be necessary in some applications to maintain noise free control lines.

Evaluation Board Schematic



Evaluation Board Layout

